

Contents of Applied Physics A 54

This listing presents the papers in alphabetical order of the first author, subdivided into the sections "Solids and Materials: Physical and Chemical Properties" and "Surfaces and Multilayers: Growth, Modification, and Integration". The Author Index that follows covers **Applied Physics A** and **B**, and is presented in tabular form. The names are listed in alphabetical order in the first column. The second and third columns contain the bibliographic data necessary to locate the paper. The issue is specified by the number separated from the volume number by a slash. The PACS numbers given in the fourth column may be used in conjunction with the PACS listing on the left to infer the topic of a paper.

Solids and Materials

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